

File View Edit Tools Window Help

Drafts

- BRS: 31 and (
- BRS: 36

Pending

Active

- L35: (1290) (base and drain and source and emitter
- L36: (132) 35 and (concentration with constant)
- L37: (10) (US-6060731-5 or US-6501128-5 or US-55369
- L38: (129) 36 not 37
- L39: (93) 38 and (collector and gate and (insulat\$4
- L40: (69) 39 and (impurity adj concentration)
- L41: (68) 40 and electrode
- L42: (48) 41 and (trench or buried)

Failed

Saved

- (1) "20040089886"
- (2) "6670658"
- (5) "6495871"
- (21) Hattori-hidetaka.in.
- (0) 6670658.URPN.
- (9266) ("IGBT" or (insulat\$3 adj gate adj bipolar a
- (38) ("IGBT" or (insulat\$3 adj gate adj bipolar adj
- (48) ("IGBT" or (insulat\$3 adj gate adj bipolar adj
- (38) ("IGBT" or (insulat\$3 adj gate adj bipolar ad

DBs: USPAT, US-PGPUB, EPQ, JPO, IBM, TDB

Default operator: OR

41 and (trench or buried)

438 items 438 items 438 items 438 items 438 items

	U	I	PT	P	Document ID	Issue Dat	Pages	Title	Current OR	Current
1	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 20040166637	20040826	33	Manufacturing method of semiconductor device	438/270	257/E21.9;
2	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 20040089886	20040513	NA	Power semiconductor element capable of improving short circuit withstand capability while maintaining low on-voltage and method of	257/279	257/E21.4;
3	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 20040061518	20040401	88	Time limit function utilization	324/765	324/464
4	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 20030205820	20031106	41	Semiconductor device and method of manufacturing the same	257/770	257/768;
5	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 20030190788	20031009	25	Semiconductor device and its manufacturing method	438/285	257/773;
6	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 20030146473	20030807	25	Semiconductor device	257/346	257/E29.3;
7	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 20030089966	20030515	65	Power semiconductor element capable of improving short circuit withstand capability while maintaining low on-voltage and method of	257/565	257/E21.6;
8	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 20030042537	20030306	76	Semiconductor device	257/328	257/329;
9	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 20030034520	20030220	58	Semiconductor device having gate electrode in which depletion layer can be generated	257/344	257/330;
10	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 20021024	20021024	58	SEMICONDUCTOR DEVICE	257/368	257/402;
									257/E21.4;	257/408;